

### INCHANGE SEMICONDUCTOR

## **isc Silicon NPN Power Transistor**

## 2SD1884

### DESCRIPTION

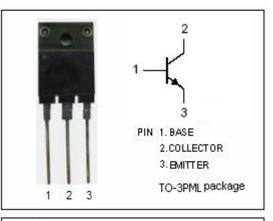
- · High Breakdown Voltage-
- : V<sub>СВО</sub>= 1500V (Min)
- High Switching Speed
- High Reliability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

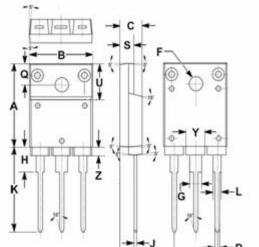
### APPLICATIONS

- Color TV horizontal deflection output
- Color display horizontal deflection output

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL		VALUE	UNIT	
	PARAMETER	VALUE		
V <sub>CBO</sub>	Collector-Base Voltage	1500	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	800	V	
V <sub>EBO</sub>	Emitter-Base Voltage	6	V	
lc	Collector Current- Continuous	5	А	
I <sub>CP</sub>	Collector Current-Pulse	20	А	
Pc	Collector Power Dissipation @ $T_c=25^{\circ}C$	60	W	
TJ	Junction Temperature	150	°C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	Ĉ	
	-	-		





R

	m	m
DIM	MIN	MAX
A	19.90	20.10
В	15.75	16.10
С	5.50	5.70
D	0.90	1.10
F	3.30	3.50
G	2.90	3.20
H	5.90	6.10
J	0.595	0.70
K	21.10	22.50
L	1.90	2.25
N	10.80	11.00
0	4.90	5.10
R	3.75	3.95
S	3.20	3.60
U	9.90	10.10
Υ	4.20	4.90
Z	1.90	2.10

isc website: www.iscsemi.com



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### ELECTRICAL CHARACTERISTICS

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	800			V
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 0.8A			5.0	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 0.8A			1.5	V
І <sub>сво</sub>	Collector Cutoff Current	V <sub>CB</sub> = 800V ; I <sub>E</sub> = 0			10	μA
Ices	Collector Cutoff Current	V <sub>CE</sub> = 1500V ; R <sub>BE</sub> = 0			1.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 4V ; I <sub>C</sub> = 0			1.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A ; V <sub>CE</sub> = 5V	8			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 4A ; V <sub>CE</sub> = 5V	5		10	
tf	Fall Time	I <sub>C</sub> = 4A , I <sub>B1</sub> = 0.8A ; I <sub>B2</sub> = -1.6A Pw=20 μ s; Duty Cycle≤1%			0.3	μ <b>S</b>

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